

## PROBLEMS

3-1.1. Show that the maximum instantaneous energy stored in the circuit of Fig. 3-1 at resonance is  $L(I_{\max})^2/2$ . Use this value in (3-4) to verify (3-5).

3-1.2. For the circuit shown in Fig. 3-1, prove that  $V_C = QV$  at the resonance frequency.

3-1.3. In the circuit of Fig. 3-1, let  $L = 100 \mu\text{H}$ ,  $C = 100 \text{ pF}$ , and  $R = 5 \text{ ohms}$ . Find:

- (a) The resonance frequency  $f_o$ .
- (b) The circuit  $Q$  at resonance.
- (c) The voltage  $V_C$  at resonance if  $V = 10 \mu\text{V}$ .

3-1.4. For the circuit values given in Problem 3-1.3, determine the values of the complex zeros ( $\gamma = \alpha \pm j\beta$ ) of input impedance  $Z(s)$ . Sketch the zero-pole diagram and show by a graphical method that the radian-frequency interval  $\omega_2 - \omega_1$  between half-power points is approximately equal to  $2\alpha$ , and that  $\beta \approx \omega_o$ . The value of  $Q$  is now approximated as  $Q \approx \beta/2\alpha$ . Would this approximation hold if  $\beta = 3\alpha$ ?

3-2.1.

(a) The circuit of Fig. 3-5 has  $R_t = 2000 \text{ ohms}$ ,  $f_o = 10^7 \text{ Hz}$ , and bandwidth  $B = 250 \text{ kHz}$ . Find the values of  $Q$ ,  $L$ , and  $C$ .

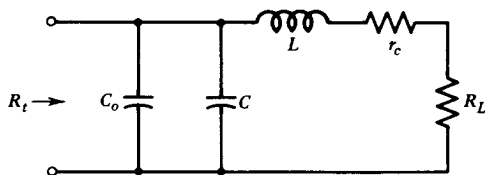
(b) If the circuit is driven with  $I = 2 \text{ mA(rms)}$ , what is the magnitude of  $I_C$ ?

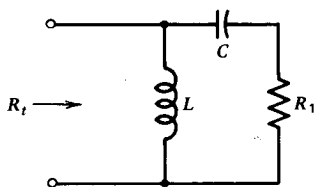
3-3.1. A tuned transistor amplifier requires a collector load resistance  $R_t = 2000 \text{ ohms}$  at  $f = 1.6 \text{ MHz}$ . The output capacitance of the transistor is  $C_o = 20 \text{ pF}$ . A load  $R_L = 5 \text{ ohms}$  is to be transformed to  $R_t$  with the circuit shown in Fig. P3-3.1.

- (a) Assume that the coil resistance  $r_c$  is negligible. Determine the values of  $L$  and  $C$  and the bandwidth  $B$ .
- (b) If the inductor in the circuit is tuned with a ferrite slug, its  $Q_L$  may be as low as 50. Find the corresponding value of  $r_c$  for the inductance value used in part (a). How will this alter the value of  $R_t$ ?
- (c) Let  $Q_L = 50$  for the coil. Solve for new values of  $L$  and  $C$  that will produce  $R_t = 2000 \text{ ohms}$ .

3-3.2. The circuit of Fig. P3-3.2 is to be designed to transform  $R_1 = 5 \text{ ohms}$

**Fig. P3-3.1**



**Fig. P3-3.2**

to  $R_i = 4 \text{ k}\Omega$  at  $f_o = 20 \text{ MHz}$ . Assume infinite  $Q_L$  for the coil. Find the values of  $L$ ,  $C$ ,  $Q_b$ , and  $B$ .

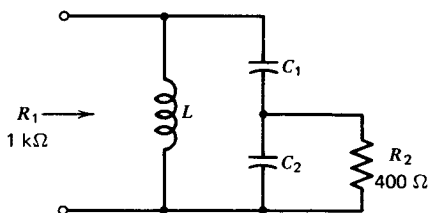
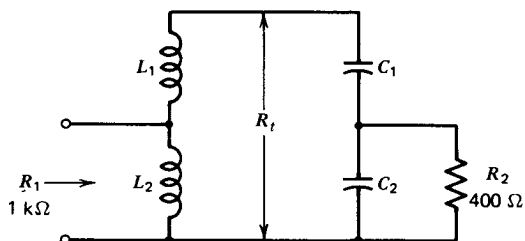
3-3.3. Use the  $L$  and  $C$  values found in Problem 3-3.2, but let the coil have a value of  $Q_L = 50$ . Find the coil resistance  $r_c$ , and the new values of  $R_b$ ,  $Q_b$ , and  $B$ .

3-3.4. If the circuit of Problem 3-3.2 is driven by a current source with internal resistance  $R_s = 6 \text{ k}\Omega$ , what is the bandwidth of the overall circuit?

3-3.5 Derive the *exact* expressions for  $\omega_o$  and  $R_i$  found in Table 3-3.2.

3-6.1. An interstage matching network is required to transform a load resistance  $R_2 = 400 \text{ ohms}$  into  $R_1 = 1 \text{ k}\Omega$  at  $f_o = 5 \text{ MHz}$  with bandwidth  $B = 50 \text{ kHz}$ . Inductance coils with  $L \approx 2 \mu\text{H}$  are desired if feasible. Neglect the coil resistance. Try the circuit of Fig. P3-6.1. Find the values of  $L$ ,  $C_1$ , and  $C_2$ .

3-6.2. The values found in Problem 3-6.1 may be unsuitable. Hence a double-tapped circuit as shown in Fig. P3-6.2 is indicated. The value of  $R_2$  is transformed up to an  $R_i$  sufficiently large to provide a reasonable value of  $L$ ,

**Fig. P3-6.1****Fig. P3-6.2**

and then transformed down to the desired  $R_1 = 1 \text{ k}\Omega$ . Assume no mutual coupling between  $L_1$  and  $L_2$ . Find  $L_1$ ,  $L_2$ ,  $C_1$ , and  $C_2$ .

3-7.1. Measured inductance values for the tapped coil shown in Fig. P3-7.1 are  $L_{12} = 4 \mu\text{H}$ ,  $L_{23} = 2 \mu\text{H}$ , and  $L_{13} = 9 \mu\text{H}$ .

(a) Find the values of the mutual inductance  $M$  and the coefficient of coupling  $k$  between the two parts of the coil.

(b) If  $V_{13} = 10$  volts is applied across the coil, what are the values of  $V_{12}$  and  $V_{23}$ ?

3-7.2. Design a tapped-coil circuit like that of Fig. 3-16 to transform  $R_2 = 10$  ohms to  $R_1 = 250$  ohms at  $f_o = 4$  MHz. Use a coil with  $L = 2 \mu\text{H}$  and coupling coefficient  $k = 0.25$ . Find the tap location and necessary tuning capacitance with the help of the curves in Section 3-7.

3-7.3. Repeat Problem 3-7.2 with  $R_2 = 50$  ohms,  $R_1 = 200$  ohms,  $f_o = 30$  MHz,  $L = 2 \mu\text{H}$ , and  $k = 0.1$ .

3-8.1. A single-tuned transformer (Fig. 3-26) is to be designed to transform  $R_2 = 1 \text{ k}\Omega$  to  $R_1 = 10 \text{ k}\Omega$  at  $f_o = 16$  MHz with bandwidth  $B = 160$  kHz.

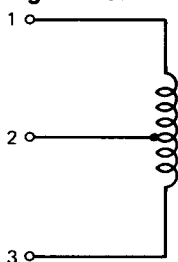
(a) Determine the values for  $L_1$ ,  $L_2$ ,  $M$ ,  $k$ , and  $C$  for  $Q_p = 1$ .

(b) Repeat for  $Q_p = 10$ .

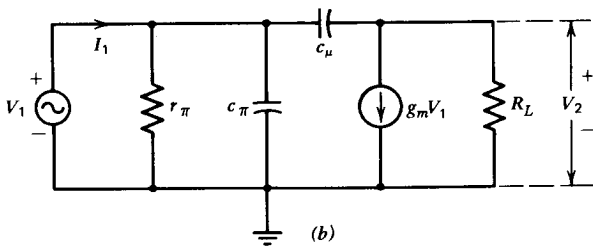
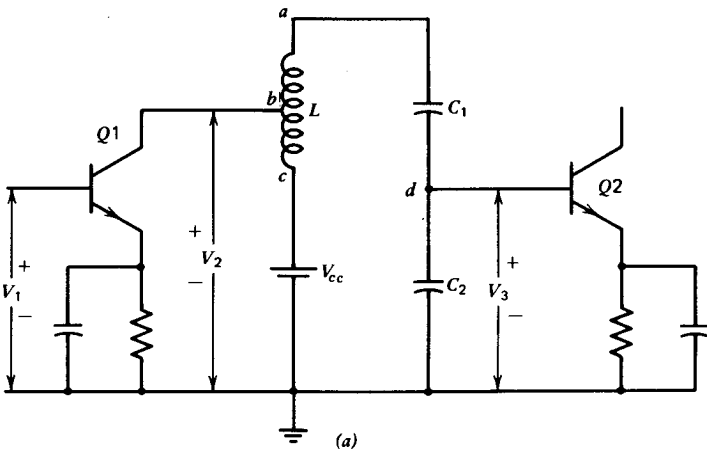
3-8.2. Solve Problem 3-6.1 by the use of a single-tuned transformer to see whether it offers any advantage.

3-8.3. Figure P3-8.3a shows two transistors coupled by an interstage matching network that is to be designed to provide a voltage gain,  $|A_v| = |V_2/V_1| = 50$ , from the base to the collector of  $Q_1$  at center frequency  $f_o = 5$  MHz, with bandwidth  $B = 50$  kHz. The collector load impedance for  $Q_2$  will be assumed identical with that for  $Q_1$  so that both stages have the same input impedance. Base-biasing resistors (not shown) are assumed to be so large that their effect can be ignored. For the desired operating point,  $V_{CE} = 10$  V and  $I_C = 1$  mA, the data sheet for the transistors gives  $h_{ie} = 2500$  ohms and  $h_{fe} = 100$ , measured at  $f = 1$  kHz. Also, for  $V_{CE} = 20$  V,  $I_C = 10$  mA, and  $f = 100$  MHz the data sheet gives  $|h_{fe}| = 3$ . At  $V_{CB} = 5$  V the value of  $C_{obo} = 4$  pF, which represents a high-side estimate of  $C_\mu$  for use in the simplified hybrid-pi equivalent circuit of Fig. 3-8.3b. (See Fig. 4-3 for more information on the hybrid-pi circuit.)

Fig. P3-7.1



**Fig P3-8.3**



- In the hybrid-pi circuit, let  $r_{\pi} = h_{ie} = 2500$  ohms and  $C_{\mu} = 4$  pF. From the above data, compute the values of  $f_T$  and  $C_{\pi}$  at  $I_C = 10$  mA. Then estimate the value of  $C_{\pi}$  and  $g_m$  at  $I_C = 1$  mA.
- From the hybrid-pi model, derive expressions for the voltage gain,  $A_v = V_2/V_1$ , and input admittance,  $Y_i = G_i + jB_i = I_1/V_1$ . Use the values from part (a) to determine the load resistance  $R_L$  needed for  $A_v = 50$  and the complex value of  $Y_i$  that results when this load is used.
- Find the equivalent parallel resistance  $R_p$  and capacitance  $C_p$  represented by  $Y_i$ . ( $Y_i = 1/R_p + j\omega C_p$ .) These values represent the load that the matching network sees between point  $d$  and ground in Fig. P3-8.3a. Similarly,  $R_L$  is the load presented to the collector of  $Q_1$  at point  $b$ .
- Choose a value for the inductance  $L$ . Assume that it has a value of  $Q_L = 200$ . Find the values of  $C_1$  and  $C_2$  to obtain the specified bandwidth. Take the coil losses into account but ignore the effect of the output impedance of  $Q_1$ .
- Find the position of the tap (point  $b$ ) on the inductor to provide the proper load for the transistor.